

1000V N-Channel MOSFET

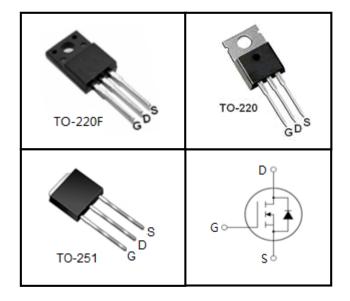
FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Package	Marking		
CS2N100F	TO-220F	CS2N100F		
CS2N100P	TO-220	CS2N100P		
CS2N100U	TO-251	CS2N100U		



Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter	Symbol	Value			Unit
		TO-220F	TO-220	TO-251	Unit
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	1000		V	
Continuous Drain Current	I _D	2		А	
Pulsed Drain Current (note1)	I _{DM}	8		A	
Gate-Source Voltage	V _{GSS}		±30		V
Single Pulse Avalanche Energy (note2)	E _{AS}	45		mJ	
Avalanche Current (note1)	I _{AS}	3		A	
Repetitive Avalanche Energy (note1)	E _{AR}	27		mJ	
Power Dissipation (T _C = 25°C)	P _D	36	75	5	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance					
Barrandar	Symbol	Value			
Parameter		TO-220F	TO-220	TO-251	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	3.47	1.67		K/W
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60		



CS2N100F,CS2N100P,CS2N100U

Specifications $T_J = 25^{\circ}C$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Value			Unit		
	Cymbol		Min.	Тур.	Max.			
Static				_	-			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	1000			V		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 1000V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA		
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 20V$	-		±100	nA		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.0	V		
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 1.0A		6	7.2	Ω		
Dynamic								
Input Capacitance	C _{iss}	- V _{GS} = 0V,		419		pF		
Output Capacitance	C _{oss}	$V_{DS} = 25V,$		45				
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		9				
Total Gate Charge	Q _g			16		nC		
Gate-Source Charge	Q _{gs}	$V_{DD} = 800V, I_D = 2.0A, V_{GS} = 15V$		2				
Gate-Drain Charge	Q _{gd}			8				
Turn-on Delay Time	t _{d(on)}			36				
Turn-on Rise Time	t _r	V _{DD} = 500V, I _D =2.0A,		12				
Turn-off Delay Time	t _{d(off)}	$V_{\text{DD}} = 500\text{V}, \text{ I}_{\text{D}} = 2.0\text{A},$ $\text{R}_{\text{G}} = 25 \ \Omega$		100		ns		
Turn-off Fall Time	t _f			43				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	۱ _s	T 05.00			2			
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			8	A		
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 1.0A, V _{GS} = 0V			1.4	V		
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 2.0A,		432.5		ns		
Reverse Recovery Charge	Q _{rr}	$di_{F}/dt = 100 \text{ J} / \mu \text{s}$		424		μC		

Notes

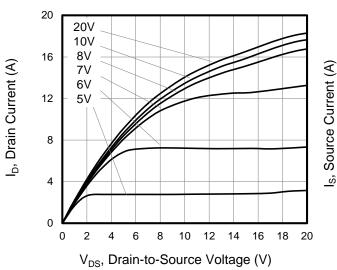
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 10.0mH, V_{DD} = 50V, R_G = 25 \Omega, Starting T_J = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%

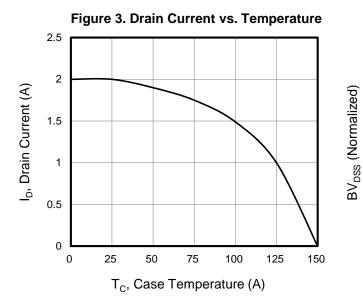


Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

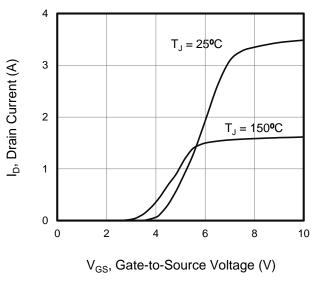
Figure 1. Output Characteristics (T_J = 25°C)

Figure 2. Body Diode Forward Voltage









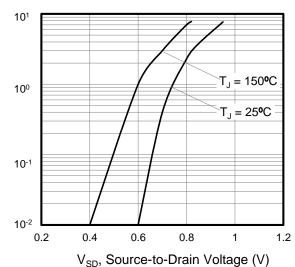
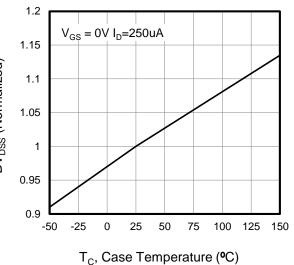
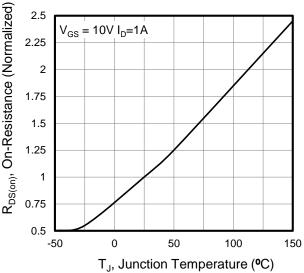


Figure 4. BV_{DSS} Variation vs. Temperature

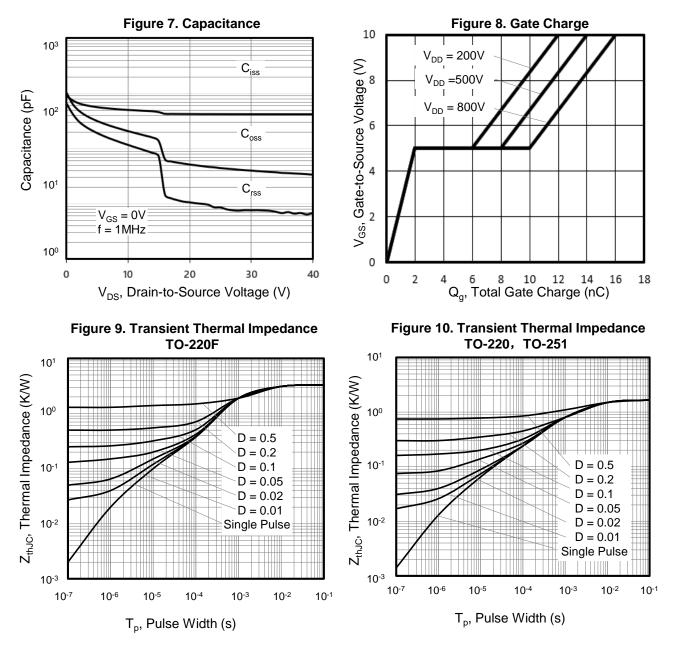








Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted







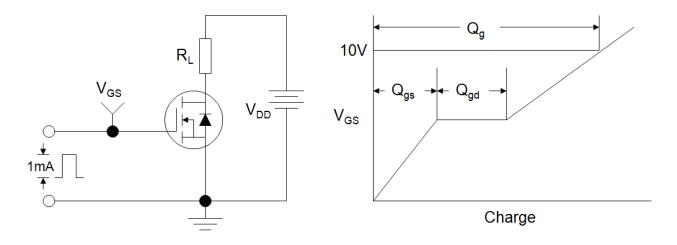


Figure B: Resistive Switching Test Circuit and Waveform

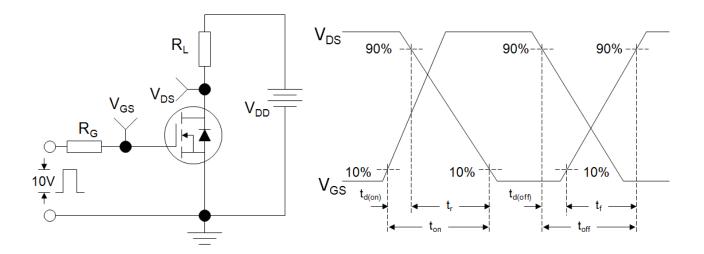
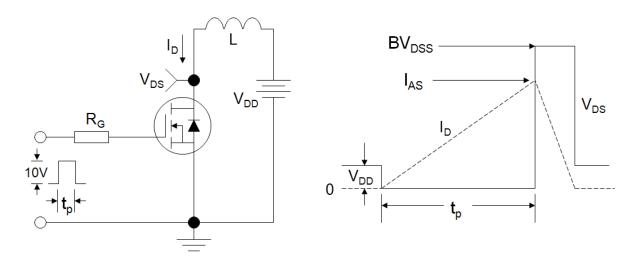


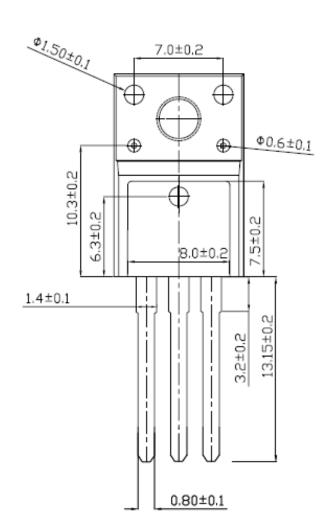
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

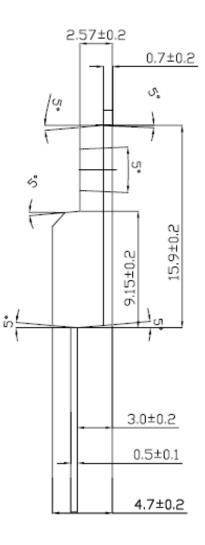






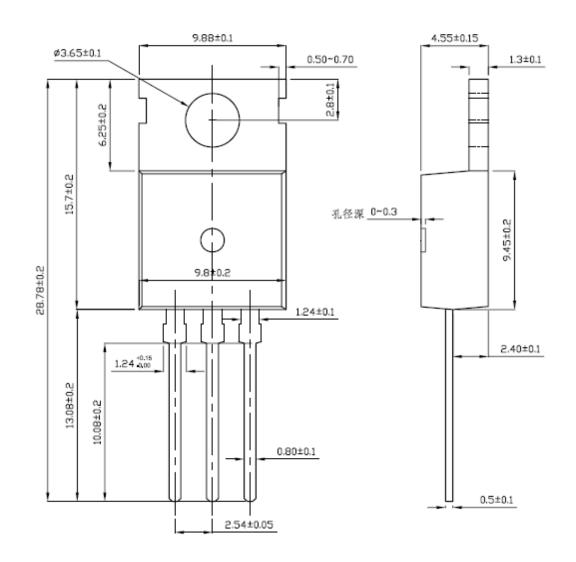
TO-220F







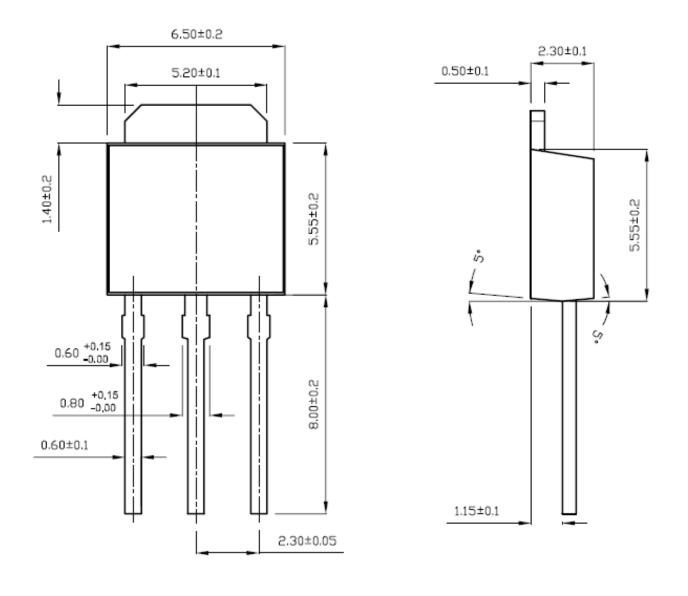
TO-220







TO-251





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